

Low-Power Linear Power Amplifier Chip

AAS3109

Product Specification

V1.0

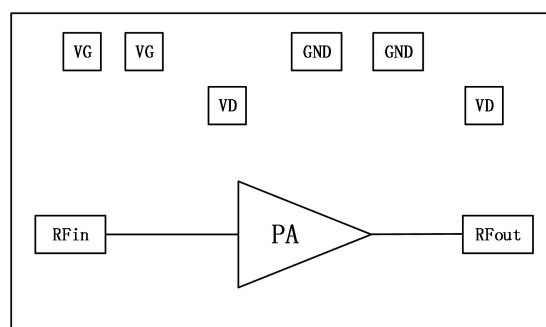
1. 产品特性

Operating Frequency: 17.5~21.5 GHz
Output 1dB Compression Point: 23.8 dBm
Output 5dB Compression Point: 24.9 dBm
Power Added Efficiency (PAE): 21.2% @ Pout = 19 dBm
Dynamic Drain Current: 173 mA @ P5dB
Operating Current: 74.0 mA @ Pout = 19 dBm
Power Gain: 17.3 dB @ Pout = 19 dBm
IMD3: -27 dBc @ Pout = 16 dBm/tone, $\Delta f = 10$ MHz
IMD3: -27 dBc @ Pout = 16 dBm/tone, $\Delta f = 400$ MHz
Input Return Loss: 10 dB
Small-Signal Gain: 17.9 dB (Typical) @ VD = 5V, IDQ = 27mA, VG = -5V
Chip Dimensions: 1.80mm × 1.16mm × 0.05mm

2. 功能概述

The AAS3109 is a GaAs low-power linear power amplifier chip operating from 17.5 GHz to 21.5 GHz. Tested under continuous wave (CW) conditions at a supply voltage of +5V, it provides a power gain of 17.3 dB with IMD3 performance of -27 dBc at an output power of 16 dBm per tone. The chip features a 50 Ω port impedance and adopts backside metal grounding.

3. Block Diagram



4. Typical Applications

Applicable to communication, radar, electronic countermeasure (ECM) and other related fields.